

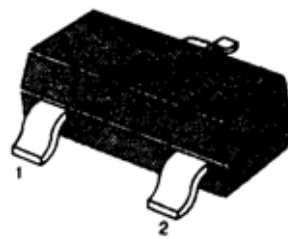
■■ APPLICATION: Interface Circuit and Driver Circuit Applications.

—NPN silicon—

■■ MAXIMUM RATINGS (Ta=25°C)

SOT-323

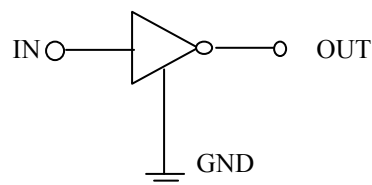
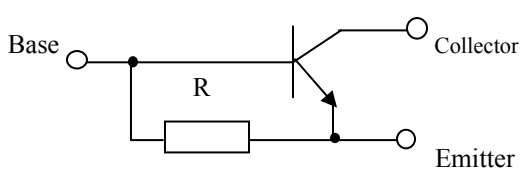
PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CB0}	50	V
Collector-emitter voltage	V _{CEO}	50	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	I _c	100	mA
Collector Power Dissipation	P _c	200	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	- 55~150	°C



1.Base 2. Emitter 3. Collector

■■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h _{FE}	30				V _{CE} = 5V, I _c = 5 mA
Input Voltage	R	7	10	13	KΩ	
Collector Cut-off Current	I _{CB0}			0.5	μA	V _{CB} = 50 V, I _E =0
Emitter Cut-off Current	I _{EBO}	300		580	μA	V _{EB} = 4V, I _c =0
Collector-Base Breakdown Voltage	BV _{CB0}	50			V	I _c = 0.05mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	50			V	I _c = 1 mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	5			V	I _E = 0.72 mA, I _c =0
Collector-Emitter Saturation Voltage	V _{CE(sat)}			0.3	V	I _c = 10 mA, I _B = 0.5 mA
Gain bandwidth product	f _T	150	250		MHz	I _c = 5mA, V _{CE} = 10 V


■■ h_{FE} Classification And Marking

Print Mark K24

Classification

 h_{FE} ≥30